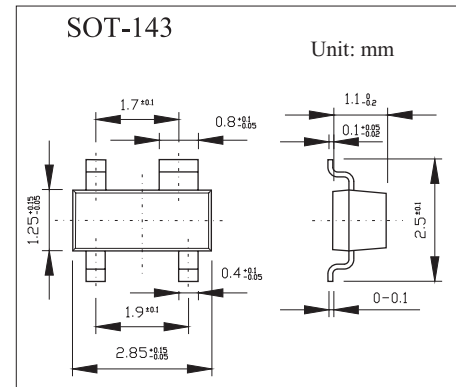


BAT62

■ Features

- Low barrier diode for detectors up to GHz frequencies.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse voltage	V _R	40	V
Forward current	I _F	20	mA
Total power dissipation, T _s ≤ 85°C	P _{tot}	100	mW
Junction temperature	T _J	150	°C
Storage temperature range	T _{stg}	-55 to + 150	°C
Junction - ambient ¹⁾	R _{th JA}	≤ 810	K/W
Junction - soldering point	R _{th JS}	≤ 650	K/W

Note

1.Package mounted on alumina 15 mm × 16.7 mm × 0.7 mm.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	I _R	V _R = 40 V			10	μ A
Forward voltage	V _F	I _F = 2 mA		0.58	1	V
Diode capacitance	C _T	f = 1 MHz; V _R = 0		0.35	0.6	pF
Case capacitance	C _c			0.1		pF
Differential resistance	R _o	V _R = 0, f = 10 KHz		225		K Ω
Series inductance	L _s			2		nH

■ Marking

Marking	62
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